

STPS30L30C

Low drop power Schottky rectifier

Features

- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop
- Low thermal resistance
- Avalanche capability specified

Description

This dual center tap Schottky rectifier is suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in TO-220AB, D²PAK and I²PAK, this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.

Table 1. Device summary

I _{F(AV)}	2 x 15 A
V _{RRM}	30 V
T _j (max)	150 °C
V _F (typ)	0.37 V

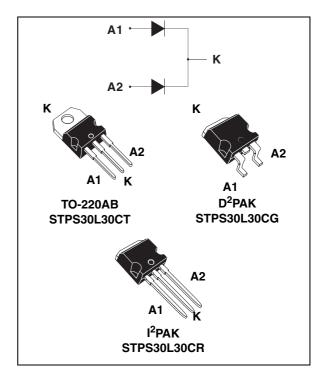
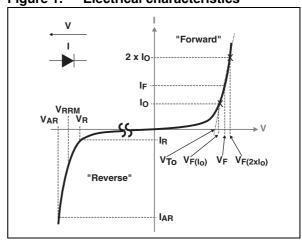


Figure 1. Electrical characteristics (a)



V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 12* V_{AR} and I_{AR} are pulse measurements (t_p < 1 μs). V_R, I_R, V_{RRM} and V_F, are static characteristics

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Characteristics STPS30L30C

1 Characteristics

Table 2. Absolute ratings (limiting values per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			30	V
I _{F(RMS)}	Forward rms current			30	Α
I _{F(AV)}	Average forward current $\delta = 0.5$	T _c = 140 °C, Per diode Per device		15 30	Α
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoida	l,	220	Α
I _{RRM}	Peak repetitive reverse current	t _p = 2 μs square, F= 1 kHz square		1	Α
I _{RSM}	Non repetitive peak reverse current	t _p = 100 μs square		3	Α
P _{ARM} ⁽¹⁾	Repetitive peak avalanche power	$t_p = 1 \ \mu s \ T_j = 25 \ ^{\circ}C$		5300	W
V _{ARM} ⁽²⁾	Maximum repetitive peak avalanche voltage	t _p < 1 μs T _j < 150 °C I _{AR} < 35 A		45	V
V _{ASM} (2)	Maximum single pulse peak avalanche voltage	t _p < 1 μs T _j < 150 °C I _{AR} < 35 A		45	V
T _{stg}	Storage temperature range			-65 to + 175	°C
Tj	Maximum operating junction temperature (3)			150	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/µs

For temperature or pulse time duration deratings, refer to Figure 4. and Figure 5.. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

Table 3. Thermal resistance⁽¹⁾

Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case	Per diode Total	1.5 0.8	°C/W
R _{th(c)}	Coupling	0.1		

^{1.} When the diodes 1 and 2 are used simultaneously: $\Delta T_j(\text{diode 1}) = P(\text{diode1}) \times R_{\text{th(j-c)}}(\text{Per diode}) + P(\text{diode 2}) \times R_{\text{th(c)}}$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾ F	Reverse leakage current $ \frac{T_j = 25 \text{ °C}}{T_j = 125 \text{ °C}} V_R = V_{RRM} $	T _j = 25 °C	V - V			1.5	mA
'R`			170	350	mA		
		T _j = 25 °C	I _F = 15 A			0.46	
V _E ⁽¹⁾	Forward voltage drop	T _j = 125 °C			0.33	0.37	v
v _F ···· Polward voltage drop	Porward voltage drop	T _j = 25 °C	I _F = 30A			0.57	'
		T _j = 125 °C			0.43	0.5	

^{1.} Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

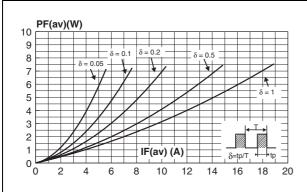
$$P = 0.24 \times I_{F(AV)} + 0.009 \times I_{F}^{2}_{(RMS)}$$

^{2.} Refer to Figure 12

^{3.} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

STPS30L30C Characteristics

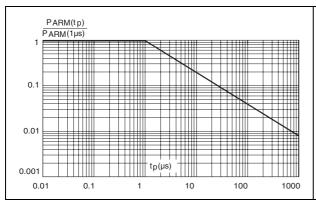
Figure 2. Average forward power dissipation Figure 3. Average forward current per diode versus average forward current per diode versus ambient temperature (per diode) $(\delta = 0.5)$



IF(av)(A) 16 Rth(j-a)=Rth(j-14 12 Rth(j-a)=15°C/W 10 8 Rth(j-a)=50°C/V 6 4 2 Tamb(°C) $\delta = tp/T$ 0 25 50 75 100 'n 125 150

Figure 4. Normalized avalanche power derating versus pulse duration

Figure 5. Normalized avalanche power derating versus junction temperature



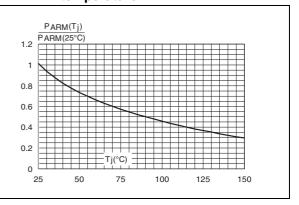
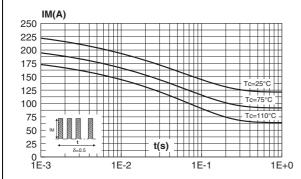
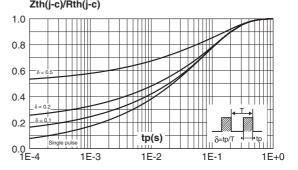


Figure 6. Non repetitive surge peak forward current versus overload duration, (maximum values per diode)

Figure 7. Relative variation of thermal impedance junction to case versus pulse duration

Zth(j-c)/Rth(j-c)

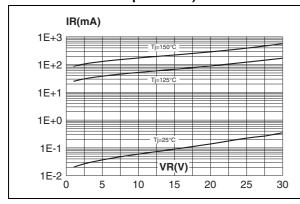




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Figure 8. Reverse leakage current versus reverse voltage applied (typical values per diode)

Figure 9. Junction capacitance versus reverse voltage applied (typical values per diode)



C(nF)
5.0

1.0

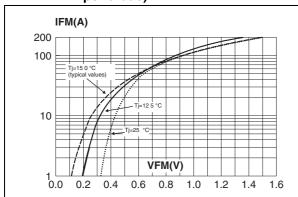
VR(V)

0.1

2 5 10 20 50

Figure 10. Forward voltage drop versus forward current (maximum values per diode)

Figure 11. Thermal resistance junction to ambient versus copper surface under tab



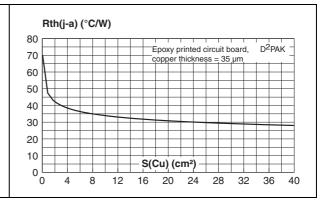
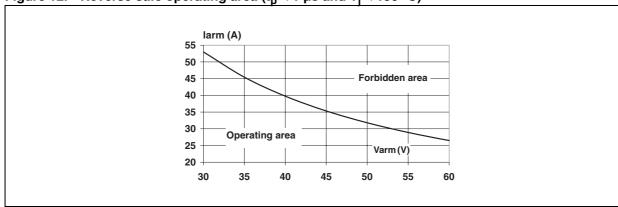


Figure 12. Reverse safe operating area (t_p < 1 μ s and T_j < 150 °C)

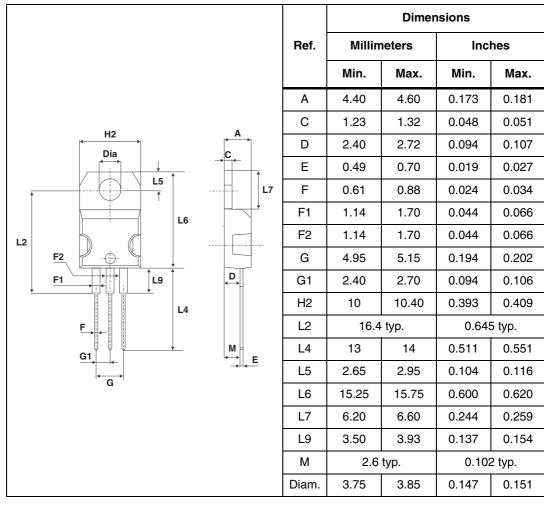


2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N⋅m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

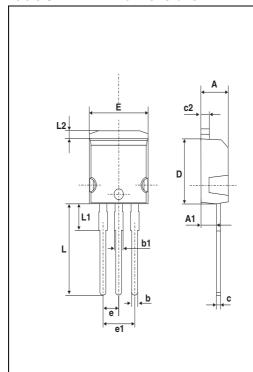
Table 5. TO-220AB dimensions



Package information STPS30L30C

Mounting (soldering) the I^2PAK metal slug (heatsink) with alloy, like a surface mount device, IS NOT PERMITTED. A standard through-hole mounting is mandatory.

Table 6. I²PAK dimensions



	Dimensions				
Ref.	Millim	neters	Inc	hes	
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.40	2.72	0.094	0.107	
b	0.61	0.88	0.024	0.035	
b1	1.14	1.70	0.044	0.067	
С	0.49	0.70	0.019	0.028	
c2	1.23	1.32	0.048	0.052	
D	8.95	9.35	0.352	0.368	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
Е	10	10.40	0.394	0.409	
L	13	14	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L2	1.27	1.40	0.050	0.055	

STPS30L30C **Package information**

D²PAK dimensions Table 7.

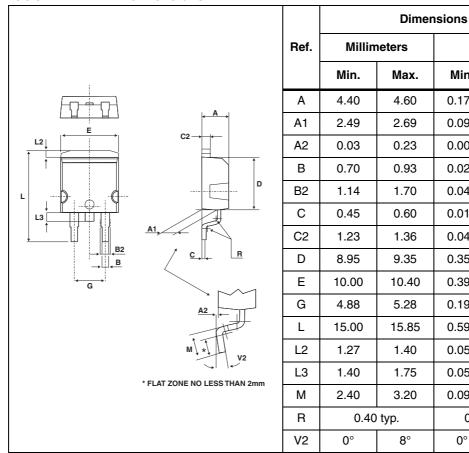
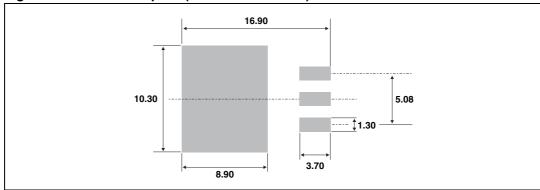


Figure 13. D²PAK footprint (dimensions in mm)



Inches

Max.

0.181

0.106

0.009

0.037

0.067

0.024

0.054

0.368

0.409

0.208

0.624

0.055

0.069

0.126

0.016 typ.

Min.

0.173

0.098

0.001

0.027

0.045

0.017

0.048

0.352

0.393

0.192

0.590

0.050

0.055

0.094

0°

Ordering information STPS30L30C

3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS30L30CT	STPS30L30CT	TO-220AB	2.0 g	50	Tube
STPS30L30CG	STPS30L30CR	D ² PAK	1.8 g	50	Tube
STPS30L30CG-TR	STPS30L30CG	D ² PAK	1.8 g	1000	Tape and reel
STPS30L30CG-TR	STPS30L30CG	I ² PAK	1.49 g	50	Tube

4 Revision history

Table 9. Document revision history

Date	Revision	Changes
Jul-2003	5C	Previous issue
29-Apr-2010	6	Added Figure 1 and Figure 12. Added parameters V _{ARM} and V _{ASM} to Table 2

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